ADE-208-352(Z)

HZM27WA
Silicon Epitaxial Planar Zener Diode for Surge Absorb

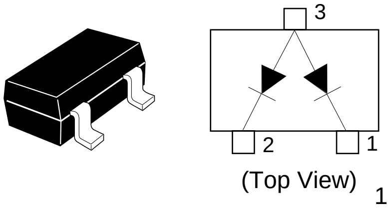
HITACHI

Rev. 0
May.1995

Features

- HZM27WA has two devices, and can absorb external + and –surge.
- MPAK Package is suitable for high density surface mounting and high speed assembly.

Outline



1 Cathode
2 Cathode
3 Anode

Ordering Information

Type No.	Laser Mark	Package Code
HZM27WA	27A	MPAK

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	$p_d{}^*$	200	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

* Two device total, See Fig. 2.

Electrical Characteristics (Ta = 25°C)

tem	Symbol	Min	Typ	Max	Unit	Test Condition
Zener voltage	V_Z	25.10	—	28.90	V	I_Z = 2 mA, 40ms pulse
Reverse current	I_R	—	—	2	µA	V_R = 21V
Capacitance	C^*	—	(27)	—	pF	V_R = 0 V , f = 1 MHz
Dynamic resistance	r_d	—	—	70	Ω	I_Z = 2 mA
ESD-Capability	—	30	—	—	KV	**C=150pF, R=330Ω Both forward and reverse direction 10 pulse

* Reference only.
** Failure criterion ; $I_R \geq 2\mu A$ at V_R = 21V.

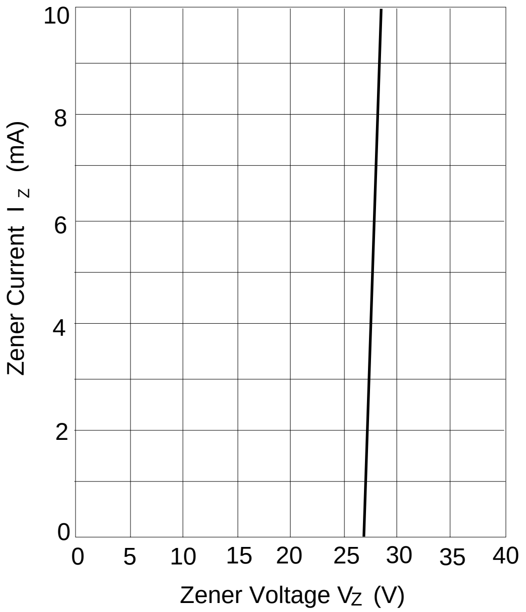


Fig.1 Zener current Vs. Zener voltage

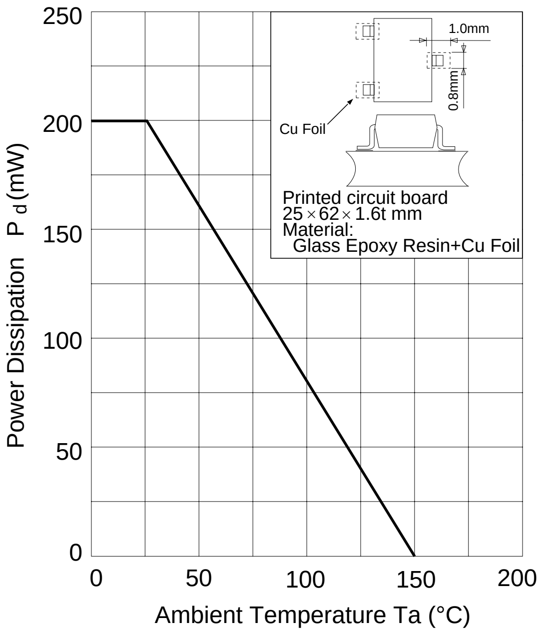


Fig.2 Power Dissipation Vs. Ambient Temperature

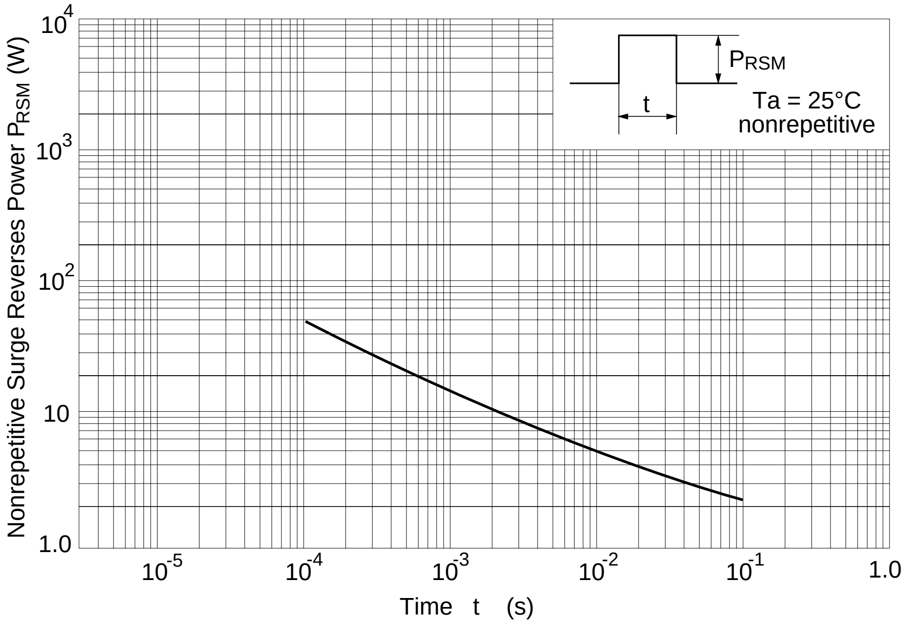


Fig.3 Surge Reverse Power Ratings

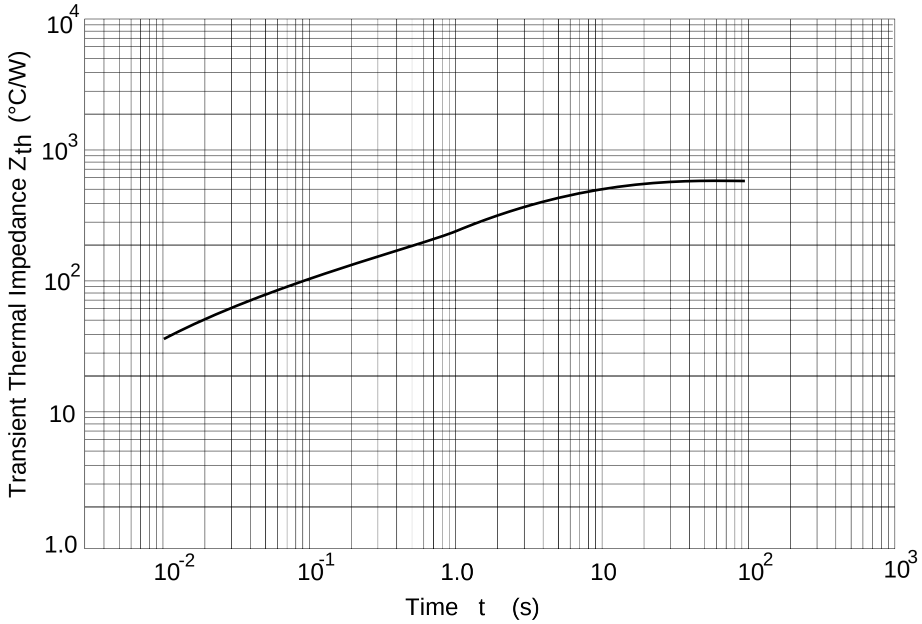
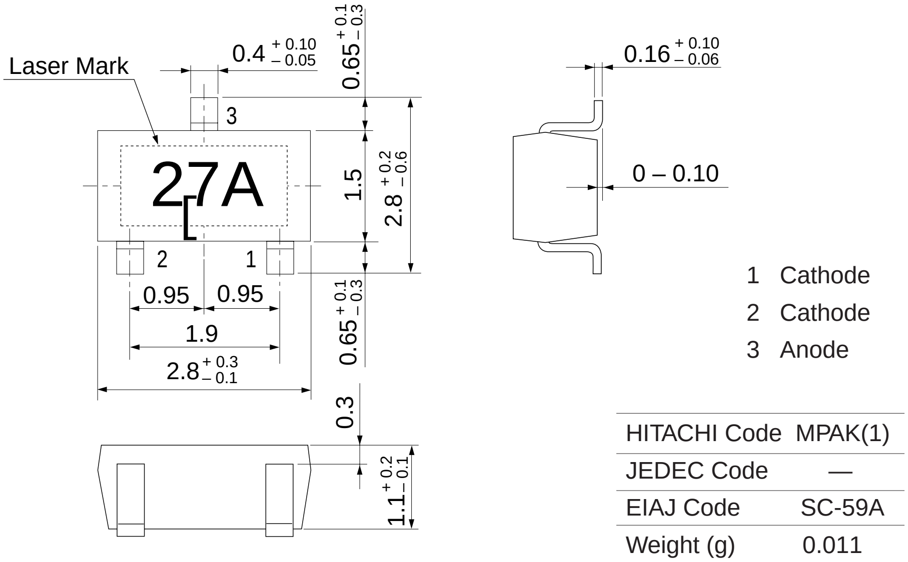


Fig.4 Transient Thermal Impedance

Package Dimensions

Unit: mm



HITACHI Code	MPAK(1)
JEDEC Code	—
EIAJ Code	SC-59A
Weight (g)	0.011